

MRI450.12-E

2 in 1 IGBT Modules

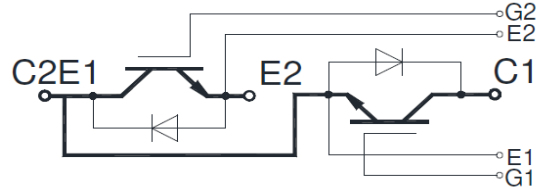


Features:

- Low V_{CEsat}
- Standard housing

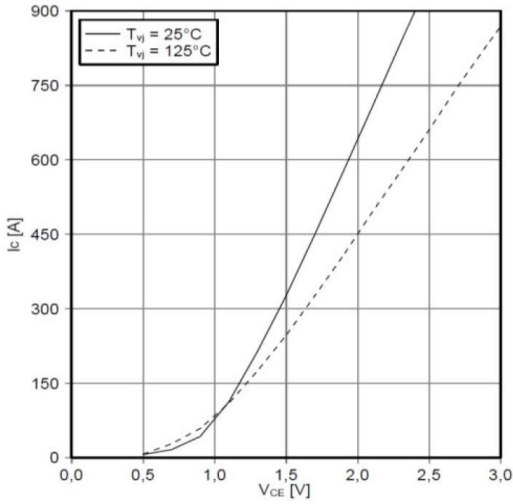
Typical applications:

- AC motor control
- Inverter and power supplies
- Motion/servo control
- Photovoltaic/Fuel cell
- Uninterruptible Power Supply System

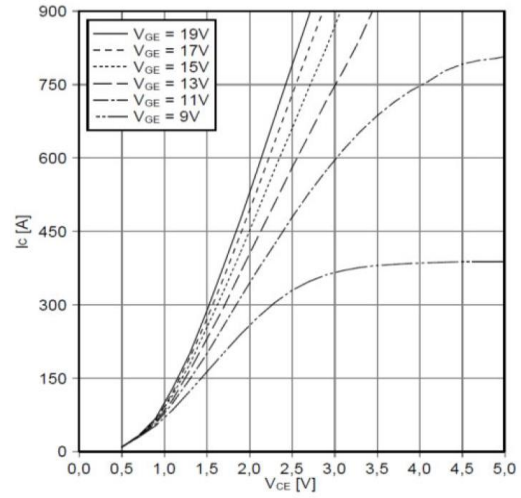


Symbol	Characteristics	Test Conditions	Value			Unit	
			Min	Typ	Max		
V_{CES}	Collector-Emitter voltage	$T_j = 25^\circ\text{C}$			1200	V	
V_{GES}	Gate-Emitter voltage	$T_j = 25^\circ\text{C}$			± 20	V	
I_C	Collector current	Continuous @ $T_c = 80^\circ\text{C}$			450	A	
I_{CM}	Repetive peak collector current	$T_p = 1\text{ ms}$			900	A	
P_C	Collector power dissipation	$T_j = 25^\circ\text{C}$, 1 device			2100	W	
T_j	Junction temperature	/	-40		125	$^\circ\text{C}$	
T_{stg}	Storage temperature	/	-40		125	$^\circ\text{C}$	
V_{ISO}	Isolation between terminal and copper base	$T_j = 25^\circ\text{C}$, AC: 1 minute	2500			V	
Screw torque	Mounting (M5)	/	3.0		6.0	N·m	
	Terminals (M6)	/	3.0		6.0	N·m	
I_{CES}	Zero gate voltage collector current	$T_j = 25^\circ\text{C}$, $V_{CE} = V_{CES}$, $V_{GE} = 0\text{V}$			5.0	mA	
I_{GES}	Gate-Emitter leakage current	$T_j = 25^\circ\text{C}$, $V_{CE} = 0\text{V}$, $V_{GE} = \pm 20\text{V}$			0.40	μA	
$V_{GE(th)}$	Gate-Emitter threshold voltage	$T_j = 25^\circ\text{C}$, $V_{CE} = 20\text{V}$, $I_C = 18\text{mA}$	5.0	5.8	6.5	V	
$V_{CE(sat)}$	Collector-Emitter saturation voltage	$T_j = 25^\circ\text{C}$, $V_{GE} = 15\text{V}$, $I_C = 450\text{A}$		1.70	2.15	V	
		$T_j = 125^\circ\text{C}$, $V_{GE} = 15\text{V}$, $I_C = 450\text{A}$		2.00		V	
R_{Gint}	Internal gate resistor	$T_j = 25^\circ\text{C}$		1.70		Ω	
C_{ies}	Input capacitance	$T_j = 25^\circ\text{C}$, $V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		32.0		nF	
C_{res}	Reverse transfer capacitance			1.50		nF	
t_{on}	Turn-on time	$V_{CC} = 600\text{V}$, $I_C = 450\text{A}$, $V_{GE} = \pm 15\text{V}$, $R_G = 1.6\Omega$, inductive load	$T_j = 25^\circ\text{C}$		250	ns	
			$T_j = 125^\circ\text{C}$		300	ns	
t_r	Turn-off time		$T_j = 25^\circ\text{C}$		90	ns	
			$T_j = 125^\circ\text{C}$		100	ns	
t_{off}	Turn-off time	$V_{CC} = 600\text{V}$, $I_C = 450\text{A}$, $V_{GE} = \pm 15\text{V}$, $R_G = 1.6\Omega$, inductive load	$T_j = 25^\circ\text{C}$		550	ns	
			$T_j = 125^\circ\text{C}$		650	ns	
t_f	Turn-off time		$T_j = 25^\circ\text{C}$		130	ns	
			$T_j = 125^\circ\text{C}$		160	ns	
E_{on}	Turn-on energy loss per pulse	$V_{CC} = 600\text{V}$, $I_C = 450\text{A}$, $L_s = 80\text{nH}$, $V_{GE} = \pm 15\text{V}$, $di/dt = 7800\text{A}/\mu\text{s}$, $R_{gon} = 1.6\Omega$	$T_j = 25^\circ\text{C}$		22	mJ	
			$T_j = 125^\circ\text{C}$		33	mJ	
E_{off}	Turn-off energy loss per pulse		$T_j = 25^\circ\text{C}$		43	mJ	
			$T_j = 125^\circ\text{C}$		65	mJ	
I_{sc}	Short circuit	$T_j = 125^\circ\text{C}$, $V_{CC} = 900\text{V}$, $V_{GE} \leq 15\text{V}$		1800		A	
V_F	Forward on voltage	$I_F = 450\text{A}$	$T_j = 25^\circ\text{C}$		1.65	2.15	V
			$T_j = 125^\circ\text{C}$		1.65		V
t_{rr}	Reverse recovery time	$I_F = 450\text{A}$	$T_j = 25^\circ\text{C}$		150	μs	
			$T_j = 125^\circ\text{C}$		210	μs	

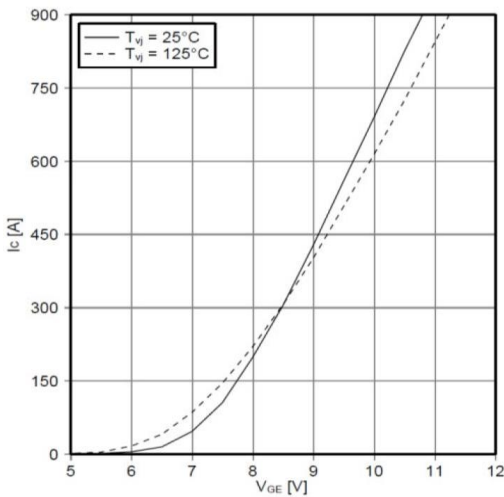
Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$R_{th(j-c)}$	Thermal resistance (1 device)	IGBT			0.06	°C/W
		FWD			0.10	°C/W
$R_{th(j-c)}$	Thermal resistance, case to heatsink	per module		0.009		°C/W
		IGBT		0.030		°C/W
		FWD		0.050		°C/W
R_{25}	Rated resistance	$T_c = 25^\circ\text{C}$		5.0		k Ω
$\Delta R/R$	Deviation of R100	$T_c = 100^\circ\text{C}$, $R_{100}=493\Omega$	-5		5	%
P_{25}	Power dissipation	$T_c = 25^\circ\text{C}$			20	mW
$B_{25/50}$	B-value	$R_2=R_{25} \exp [B_{25/50} (1/T_2-1/(298,15 \text{ K}))]$		3375		K
$B_{25/80}$	B-value	$R_2=R_{25} \exp [B_{25/80} (1/T_2-1/(298,15 \text{ K}))]$		3411		K
$B_{25/100}$	B-value	$R_2=R_{25} \exp [B_{25/100} (1/T_2-1/(298,15 \text{ K}))]$		3433		K
L_{sCE}	Stray inductance module			20		mH
R_{CC+EE}	Module lead resistance, terminals - chip	$T_c = 25^\circ\text{C}$, per switch		1.10		m Ω
W_t	Weight				345	g
Outline	454H3P					



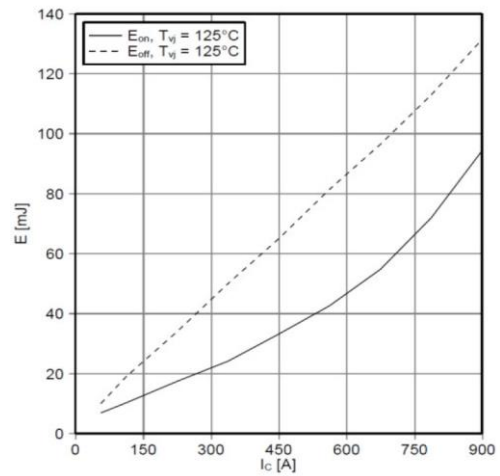
output characteristic IGBT, Inverter (typical)



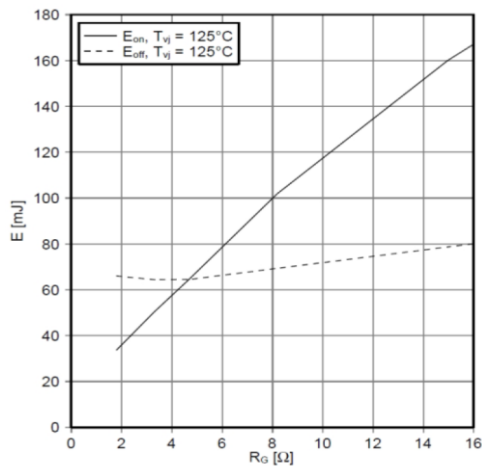
output characteristic IGBT, Inverter (typical)



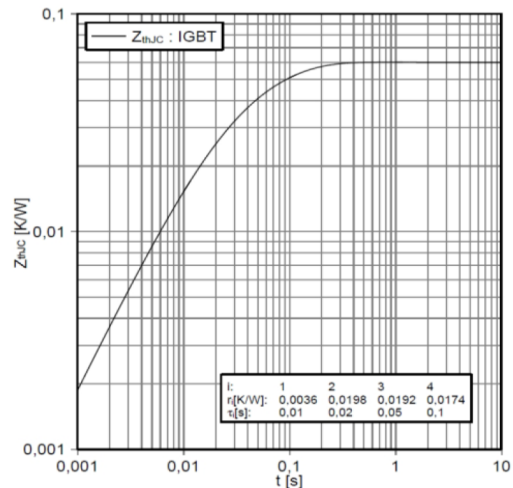
transfer characteristic IGBT, Inverter (typical)



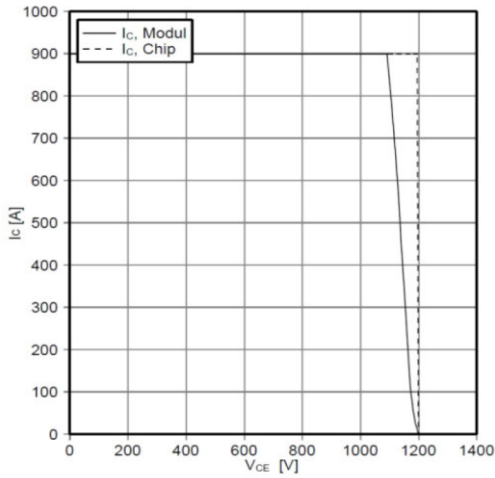
switching losses IGBT, Inverter (typical)



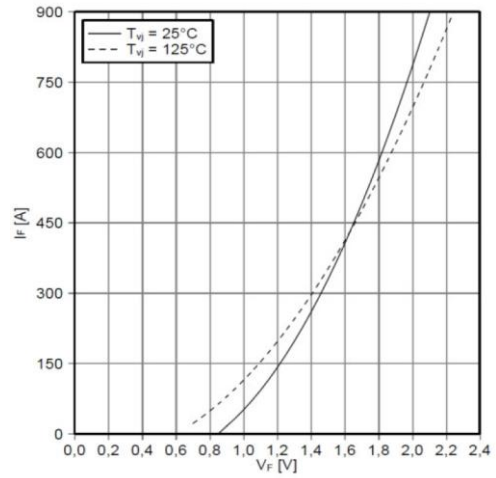
switching losses IGBT, Inverter (typical)



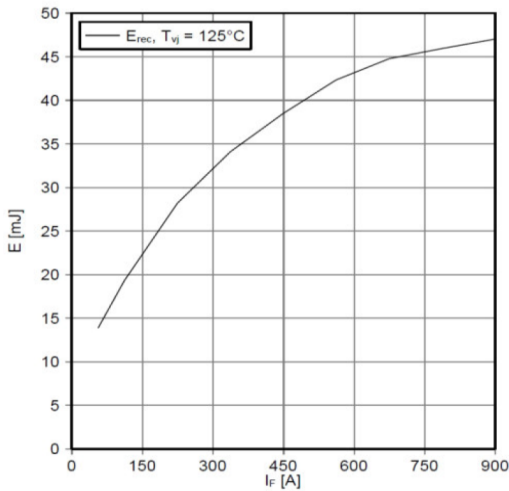
transient thermal impedance IGBT, Inverter



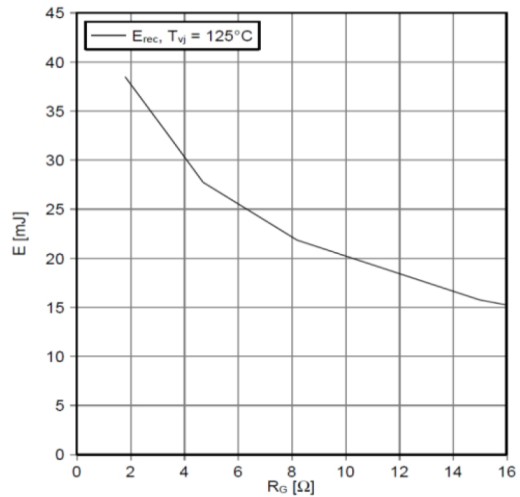
reverse bias safe operating area IGBT, Inverter (RBSOA)



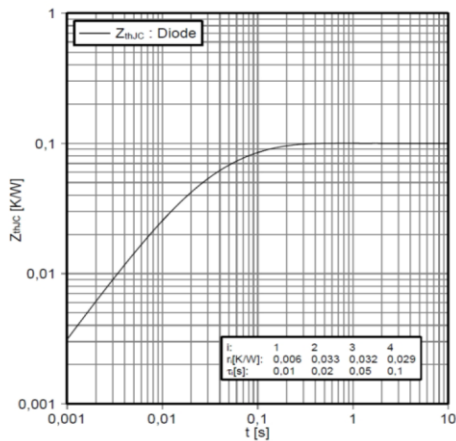
forward characteristic of Diode, Inverter (typical)



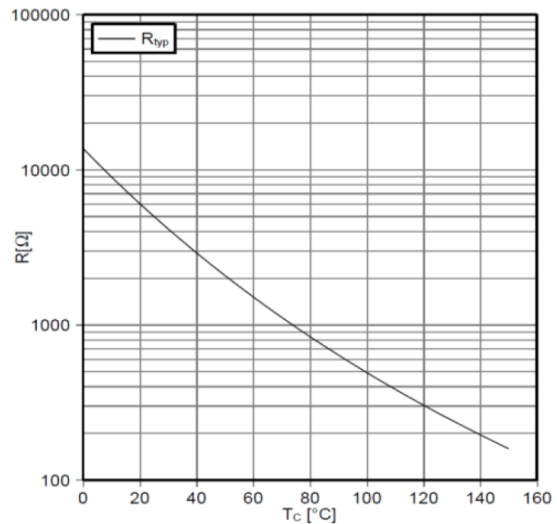
switching losses Diode, Inverter (typical)



switching losses Diode, Inverter (typical)

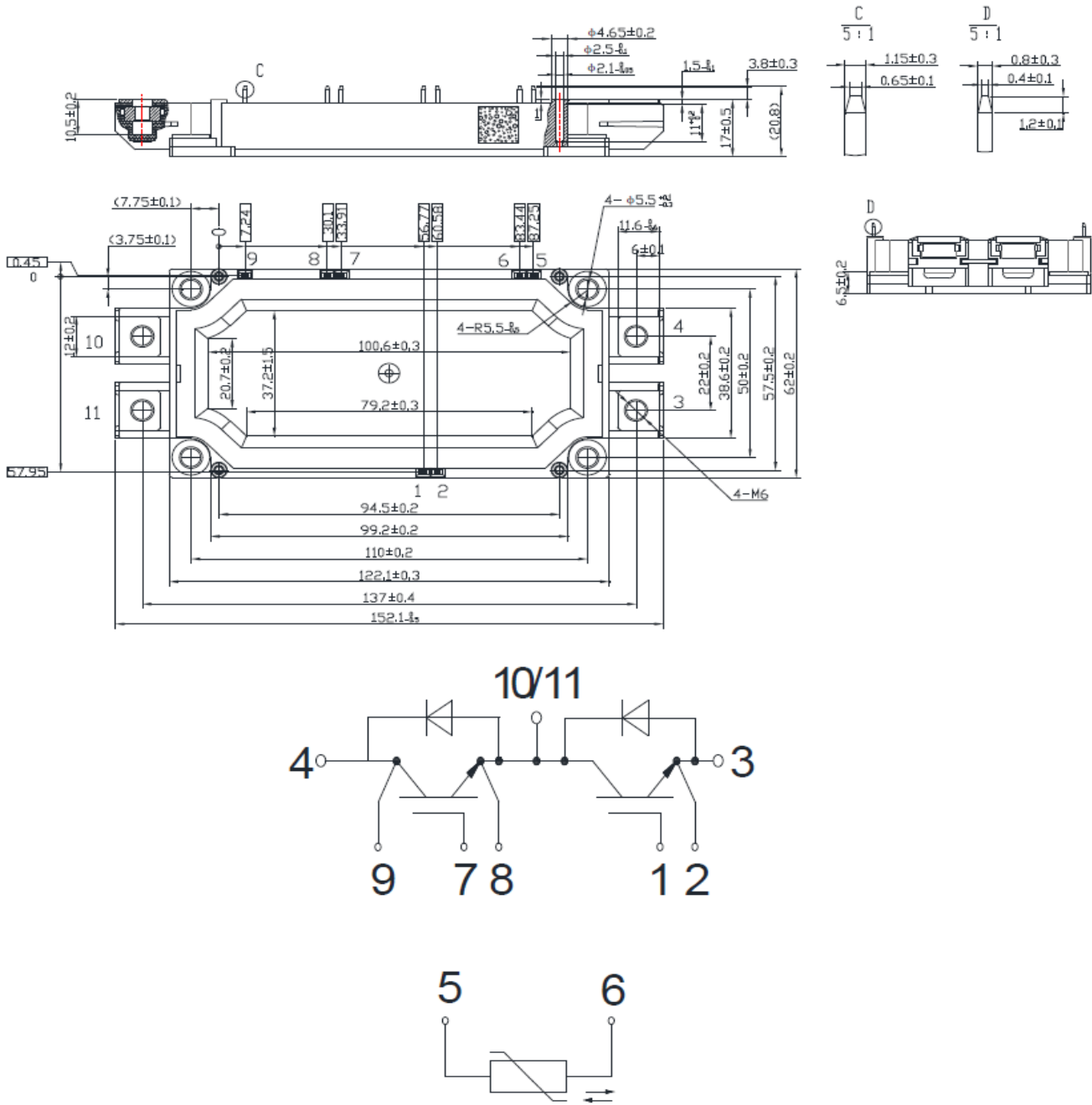


transient thermal impedance Diode, Inverter



NTC-Thermistor-temperature characteristic (typical)

Outline:



(dimensions in mm)

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